

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	40	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	1.5	kV

ELECTRICAL CHARACTERISTICS($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	80	mA
				200	
I_H	$I_T=500mA$		MAX.	100	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	2000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$ $T_j=125$		MIN.	25	A/ms
t_{on}	$I_G=80mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS
Symbol

FIG.1: Maximum power dissipation versus RMS on-state current

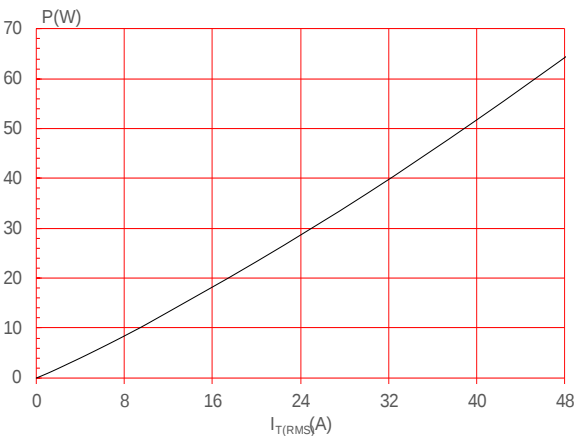


FIG.3: Surge peak on-state current versus number of cycles

FIG.2: RMS on-state current versus case temperature

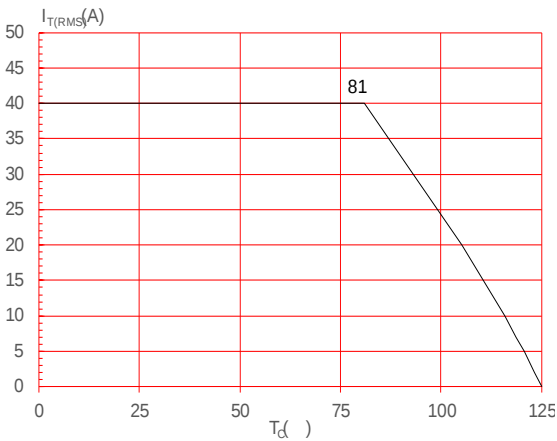


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-

ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST41Z-800BW	800	50	TO-3P(Ins)	30	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA

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